Tunable superconductivity in electron- and hole-doped Bernal bilayer graphene

Chushan Li^{1,2}, Fan Xu¹, Bohao Li³, Jiayi Li¹, Guoan Li⁴, Kenji Watanabe⁵, Takashi Taniguchi⁶, Bingbing Tong⁴, Jie Shen⁴, Li Lu^{4,7}, Jinfeng Jia^{1,2,7,8}, Fengcheng Wu^{3,9*}, Xiaoxue Liu^{1,2,7,8*}, and Tingxin Li^{1,2,7*}

¹Key Laboratory of Artificial Structures and Quantum Control (Ministry of Education), School of Physics and Astronomy, Shanghai Jiao Tong University, Shanghai 200240, China

²Tsung-Dao Lee Institute, Shanghai Jiao Tong University, Shanghai, 201210, China

³School of Physics and Technology, Wuhan University, Wuhan 430072, China

⁴Beijing National Laboratory for Condensed Matter Physics and Institute of Physics, Chinese Academy of Sciences, Beijing 100190, China

⁵Research Center for Electronic and Optical Materials, National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-0044, Japan

⁶Research Center for Materials Nanoarchitectonics, National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-0044, Japan

⁷Hefei National Laboratory, Hefei 230088, China

⁸Shanghai Research Center for Quantum Sciences, Shanghai 201315, China

⁹Wuhan Institute of Quantum Technology, Wuhan 430206, China

*Emails: wufcheng@whu.edu.cn, xxliu90@sjtu.edu.cn, txli89@sjtu.edu.cn

Graphene-based, high quality two-dimensional electronic systems have emerged as a highly tunable platform for studying superconductivity¹⁻²¹. Specifically, superconductivity has been observed in both electron-doped and hole-doped twisted graphene moiré systems¹⁻¹⁷, whereas in crystalline graphene systems, superconductivity has so far only been observed in hole-doped rhombohedral trilaver¹⁸ and hole-doped Bernal bilaver graphene (BBG)¹⁹⁻²¹. Recently, enhanced superconductivity has been demonstrated^{20,21} in BBG due to the proximity with a monolayer WSe₂. Here, we report the observation of superconductivity and a series of flavor-symmetry-breaking phases in both electron- and hole-doped BBG/WSe2 device by electrostatic doping. The strength of the observed superconductivity is tunable by applied vertical electric fields. The maximum Berezinskii-Kosterlitz-Thouless (BKT) transition temperature for the electron- and hole-doped superconductivity is about 210 mK and 400 mK, respectively. Superconductivities emerge only when applied electric fields drive BBG electron or hole wavefunctions toward the WSe₂ layer, underscoring the importance of the WSe₂ layer in the observed superconductivity. We find the hole-doped superconductivity violates the Pauli paramagnetic limit, consistent with an Ising-like superconductor. In contrast, the electron-doped superconductivity obeys the Pauli limit, even though the proximity induced Ising spin-orbit coupling is also notable in the conduction band. Our findings highlight the rich physics associated with the conduction band in BBG, paving the way for further studies into the superconducting mechanisms of crystalline graphene and the development of novel superconductor devices based on BBG.

Introduction

Although intrinsic spin-orbit-coupling (SOC) effects are negligible in graphene, SOC can be induced through the proximity effect by directly contacting graphene with transition metal dichalcogenide layers²²⁻²⁵. Experimentally, such van der Waals SOC proximity method has been demonstrated as an important tuning knob for engineering the physical properties of graphene-based systems^{13,14,20,21,26-34}. For example, the proximity-induced Ising SOC is considered as a key factor in stabilizing the superconducting state in BBG/WSe₂ heterostructures^{20,21}. However, the specific pairing mechanisms of superconductivity in both graphene moiré systems and crystalline graphene systems are still an ongoing research topic³⁵⁻³⁷. On the other hand, in crystalline graphene, although the interaction-driven flavor-symmetry-breaking phases have been observed in both conduction band (CB) and valence band (VB)^{38.45}, superconductivity has so far only been observed in the VB¹⁸⁻²¹. Here we report the observation of tunable superconductivity in BBG/WSe₂ system. Benefiting from the high vertical electrical displacement field *D* achievable in the device, the electron-doped superconductivity is observed for the first time in crystalline graphene.

Electron- and hole-doped Superconductivities

The geometry of BBG/WSe₂ device is shown in Fig. 1a, where the dual gates of V_{top} and V_{back} allow for independent control of D and carrier density n in BBG (Methods). Figure 1d shows the longitudinal resistance R_{xx} as a function of D and n at zero magnetic field, covering both the electron- and hole-doped regions. In the measured D and n ranges, the WSe₂ layer is kept as charge neutral due to the type-I band alignment shown in Fig. 1b (Methods). A series of phase transitions featured with peaks or dips in R_{xx} can be observed in the R_{xx} -D-n map. Figure 1e illustrates the corresponding phase diagram based on Fig. 1d and Fermi surface analysis via quantum oscillations. Notably, the measured R_{xx} exhibits clear electron-hole asymmetry and D-field asymmetry. The electron-hole asymmetry is associated with the asymmetric band structure of the CB and VB in BBG (Fig. 1c). The D-field asymmetry is related to the fact that the proximity induced Ising SOC effect is only significant on the top graphene layer which is closer to the WSe₂ layer^{20,21,23,24,31}. In our device, at positive (negative) D, hole wavefunctions concentrate at the top (bottom) layer of the BBG, and electron wavefunctions concentrate at the bottom (top) layer of the BBG. Therefore, notable spin splitting is either in the CB (D < 0) or in the VB (for D > 0), as

illustrated in Fig. 1c. Experimentally, the estimated Ising SOC strength λ_I is around 1.7 meV in our device (Extended Data Fig. 1).

Remarkably, two notable superconducting regions at finite doping emerge in the *n*-*D* phase diagram, one is at positive D with hole doping, and another is at negative D with electron doping. Both regions correspond to the case that doped carriers are polarized to the top graphene layer. The hole-doped superconductivity initiates at about 0.85 V/nm, which is consistent with the previous observations^{20,21}, while the electron-doped superconductivity initiates at a negative $D \sim -1.25$ V/nm. Both the electron and hole superconducting states move to the higher doping density with increasing |D|. The strength of the superconductivity, characterized by the critical current I_c and the critical temperature T_c , can be effectively tuned by applied D. Figure 1f and 1i show the differential resistance (dV_{xx}/dI_{dc}) versus dc bias current (I_{dc}) of the hole- and electron-doped superconducting states at various D, respectively. On the hole-doped side, both I_c and T_c show nonmonotonic dependence on D (Fig. 1g). At the optimal D and n of the hole-doped superconductivity, $T_{\rm c}$ (determined by 50% of the normal state resistance) is about 450 mK (Fig. 1h). Moreover, $T_{\rm BKT}$ is estimated to be about 400 mK by fitting the nonlinear *I-V* traces (Extended Data Fig. 2), which is about 1.7 times higher than previous studies^{20,21}. Additionally, the critical current densities are significantly larger than previous reports^{20,21} (Methods). On the electron-doped side, within the achievable range of D, I_c and T_c increase with increasing of |D| but exhibit a saturating trend (Fig. 1j). The maximum T_c and T_{BKT} is about 300 mK and 210 mK, respectively (Fig. 1k).

In crystalline graphene systems, the emergence of flavor-symmetry-breaking phases and superconductivity is considered to be associated with the van Hove singularities (VHS), characterized by divergent single-particle density of states (DOS), near the band edge. Extended Data Fig. 3 illustrates the calculated single-particle DOS of BBG at various displacement fields. First of all, both the CB and VB exhibit clear VHS, but at a given D, the VHS in the CB locates at lower carrier densities. At relatively small D-fields, the VHS is more pronounced in the VB, whereas at larger D, the VHS becomes stronger in the CB. These results are consistent with our observations that the flavor-symmetry-breaking phases emerge at lower *n* and larger *D* on the electron-doped side. Secondly, although the carrier density corresponding to the VHS increases monotonically with increasing D, the magnitude of DOS near VHS reach its maximum at certain D values. Since the effective Coulomb interactions are reduced at higher carrier density due to screening, the dependence of VHS on D shown in Extended Data Fig. 3 indicates that there is an optimized D-field range for engineering correlation physics in BBG. This aligns with the experimental observation that both superconductivities and symmetry-breaking states appear within a specific *D*-field range.

Quantum oscillations on the hole-doped side

Investigating quantum oscillations can provide important information of Fermi surface structures. Figure 2a displays the measured R_{xx} as a function of perpendicular magnetic

field B_{\perp} and *n* at D = 1.1 V/nm on the hole-doping side. Several sets of quantum oscillations can be distinguished through Fast Fourier transform (FFT) of R_{xx} (1/ B_{\perp}), as shown in Fig. 2c. The frequency f_v is normalized by the total carrier density, representing the fraction of the total Fermi surface area enclosed by a given cyclotron orbit (Methods).

The results at D = 1.1 V/nm near the hole-doped superconducting region closely resemble those reported in previous studies^{20,21}. In short, at hole densities lower than the superconducting region, two frequencies with $f_v^{(1)} > 1/12$ and $f_v^{(2)} < 1/12$ can be identified, indicating a state with six smaller Fermi pockets and six larger Fermi pockets. In contrast, at D = -1.1 V/nm, the FFT frequency peak only occurs at $f_y = 1/12$ (Extended Data Fig. 4), corresponding to the spin and valley symmetric Fermi surface with 12 degeneracies resulting from trigonal warping⁴⁶. This is consistent with the scenario that the WSe_2 induced Ising SOC lifts the spin and valley degeneracy of the BBG valence band at positive D. Inside the superconducting region, FFT analysis of quantum oscillations for the normal state shows spectral weight mostly concentrate at frequency slightly less than 1/2 and at low frequencies, corresponding to a partial isospin-polarized phase with two major Fermi pockets and multiple minor Fermi pockets (denoted as PIP₂ phase), consistent with the prior reports^{20,21}. Interestingly, with further increasing hole doping beyond the PIP₂ phase, the system evolves into a state with four annular Fermi surfaces, which is evident by two FFT frequency peaks satisfying $f_v^{(1)} - f_v^{(2)} = 1/4$. The annular Fermi surface is also evident in Fig. 2a that a set of electron-like Landau fan emerges at $n \sim -1.3 \times 10^{12}$ cm⁻². Note that in RTG, superconductivity emerges from an annular Fermi sea, near a PIP₂ phase¹⁸. Here, the BBG/WSe₂ system exhibits similar Fermi surface conditions but lacks an observable superconducting phase in the annular Fermi sea, highlighting a significant distinction between these two systems. The results at D = 1.19 V/nm are essentially similar to those observed at D = 1.1 V/nm, while an additional R_{xx} dip emerges at low densities (Extended Data Fig. 5).

When the applied *D*-field is beyond 1.4 V/nm, the hole-doped superconductivity vanishes. Simultaneously, the Fermi surface structures become less complex. Extended Data Fig. 4b and 4d display the quantum oscillations at D = -1.5 V/nm and its corresponding FFT, respectively. A single frequency peak at $f_v = 1/12$, resulting from trigonal warping, is observed over a wide density range at D = -1.5 V/nm. At D = 1.5 V/nm, due to the SOC-induced spin splitting in VB, the 12 degenerated Fermi pockets transform into six smaller Fermi pockets and six bigger Fermi pockets (Fig. 2d). In general, no superconductivity and flavor-symmetry-breaking states are observed at $D = \pm 1.5$ V/nm, likely due to the weakened VHS and interaction effects at such a high *D*-field, as discussed above.

Quantum oscillations on the electron-doped side

Figure 3a and 3b present the R_{xx} as a function of B_{\perp} and *n* for electron doping at D = 1.55 V/nm and -1.55 V/nm, respectively. Their FFT results are shown in Fig. 3c and 3d correspondingly. At D = 1.55 V/nm and high electron densities, the Fermi surface is spin

and valley symmetric with fourfold degeneracy ($f_v = 1/4$), as expected for a simplest graphene system without flavor-symmetry-breaking and trigonal-warping effects. With decreasing electron densities, spontaneous flavor symmetry breaking occurs, reducing the Fermi surface degeneracy to two-fold then finally to one-fold. These results resemble the half-metal and quarter-metal phases reported in rhombohedral trilayer³⁸, tetralayer⁴², and pentalayer graphene⁴³. Importantly, in between of the normal metal phase (4-fold degeneracy) and the half-metal phase (2-fold degeneracy), as well as in between of the half-metal phase and the quarter-metal phase (1-fold degeneracy), we observe partially isospin polarized Fermi surfaces (PIP₁ and PIP₂) similar to the hole-doped case. At D = -1.55 V/nm, the observed Fermi surface structures with tuning electron density are quite similar to the D = 1.55 V/nm case, except that SOC plays an important role at D = -1.55V/nm, which can be identified from the FFT frequency peak splitting around $f_v = 1/4$ in the normal metal phase (Fig. 3d). Note that in the phase with $f_v = 1/2$, no FFT frequency peak splitting around $f_v = 1/2$ can be observed, indicating two Fermi pockets with identical area. The evolution of Fermi surface with electron doping density is qualitatively captured by our theoretical calculations (Extended Data Fig. 6). Remarkably, akin to the hole-doped superconductivity, electron-doped superconductivity again only emerges when electron wavefunctions are tuned close to the WSe₂ layer, and it also originates from normal states possessing a PIP₂ Fermi surface. In RTG, PIP₁ and PIP₂ Fermi sea have not been reported in the CB^{18,38}, which could provide a clue to the absence of superconductivity in electrondoped RTG. The evolution of Fermi surface with changing electron densities at $D = \pm 1.64$ V/nm (Extended Data Fig. 8) closely resemble those observed at $D = \pm 1.55$ V/nm.

At |D| < 1.25 V/nm, superconductivity is not observed on the electron-doping side, but the flavor-symmetry-breaking phases persist to lower *D*. Extended Data Fig. 7 shows quantum oscillations and their FFT results at $D = \pm 1.1$ V/nm. The half-metal and quarter-metal phases can be clearly identified from the FFT results. However, at $D = \pm 1.1$ V/nm, the PIP₁ phase is absent and the electron density range of the PIP₂ phase become much narrower compared to that at $D = \pm 1.64$ and ± 1.55 V/nm, which is also consistent with the theoretically calculated results (Extended Data Fig. 6). These observations again indicate the importance of the PIP Femi sea for superconducting pairing in this system.

Response to in-plane magnetic field

Although the electron-doped and the hole-doped superconductivity in BBG/WSe₂ system seems have similar origin from the Fermi surface analysis, their response to in-plane magnetic field is quite different. Figure 4a and 4b show R_{xx} as a function of n and T at D = 0.96 V/nm (hole-doped) and D = -1.64 V/nm (electron-doped), respectively. The superconducting paring strength is comparable at D = 0.96 V/nm on the hole-doping side and at D = -1.64 V/nm on the electron-doping side, as evidenced by similar values of T_c and the critical perpendicular magnetic field B_{L} (Fig. 4c and 4d). Nevertheless, their response to the in-plane magnetic field B_{\parallel} differs significantly, as shown in Fig. 4e and 4f. The hole-doped superconductivity is resilient to applied $B_{\parallel} = 1$ T within a certain range of

n, while the electron-doped superconductivity is completely suppressed at a much lower $B_{\parallel} \sim 0.2$ T.

For two-dimensional spin-singlet superconductors, the suppression of superconductivity in the presence of external $B_{||}$ is primarily attributed to Zeeman effect. This gives an upper bound of the critical in-plane magnetic field $B_{c||}$, known as the Pauli paramagnetic limit B_p . For weakly-coupled BCS superconductors, $B_p = 1.86 (T/K) \times T_c^0$ with g-factor = 2, where T_c^0 is the critical temperature at zero magnetic field. Figure 4g and 4h depict the Pauli violation ratio (PVR) $B_{c||}^0/B_p$ as a function of carrier density at D = 0.96 V/nm and D = -1.64 V/nm, respectively. The critical in-plane magnetic field at the zero-temperature limit $B_{c||}^0$ is obtained by fitting the $B_{c||}(T)$ versus the temperature to the phenomenological formula $T/T_c^0 = 1$ - $(B_{c||}/B_{c||}^0)^2$ (see Extended Data Fig. 9). The ratio of $B_{c||}^0/B_p$ over the hole-doped superconducting dome changes from ~2.4 to ~1.7 with increasing hole doping, explicitly violating the Pauli paramagnetic limit. On the contrary, the electron-doped superconductivity obeys the Pauli paramagnetic limit with $B_{c||}^0/B_p < 1$ across the whole superconducting dome.

The hole-doped superconductivity is consistent with the phenomenology of Ising superconductivity⁴⁷⁻⁴⁹, which results from the proximity-induced Ising SOC by WSe₂, consistent with previous reports^{20,21}. However, the limited resilience to B_{\parallel} observed in electron-doped superconductivity is more puzzling, as a comparable Ising SOC effect is evident in the CB of BBG/WSe₂ at negative *D* fields. This requires a different scenario than the spin-valley locking picture from typical Ising superconductors. For example, more complicated scenarios such as intervalley coherent states may need to be considered²⁰. On the other hand, Rashba SOC and in-plane orbital effects could also compete with Ising SOC, leading to the observed suppression of the $B_{c\parallel}$. However, to align with the experimental observations, it is necessary for the Rashba SOC and/or in-plane orbital effects to have important differences in the electron-doped and hole-doped superconductors. Further theoretical and experimental studies are required to understand the underlying mechanism of the reduced PVR for electron-doped superconductivity in BBG/WSe₂ system.

Conclusions

Understanding the superconducting pairing mechanism in both crystalline graphene systems and twisted graphene systems remains as one of the most important and intriguing problems in condensed matter physics. Among all of graphene-based superconductors, BBG offers the simplest platform to study the mystery of the emergent superconductivity. Additionally, the structurally stable nature of BBG is a notable advantage compared to other graphene superconductors, enabling the reproducible fabrication of high-quality devices. We have revealed a rich phase diagram tuned by n and D for both the hole- and electron-doped BBG proximitized with a monolayer WSe₂. The flavor-symmetry-breaking

phases emerge at large *D*-fields in BBG closely resemble those observed in rhombohedralstacked multilayer graphene. Both the hole- and electron-doped superconductivity are associated with the emergence of PIP₂ Fermi surfaces and the proximity to WSe₂. Our results highlight the rich physics associated with the CB in BBG, revealing both the similarities and differences between the electron- and hole-doped superconductivity in BBG/WSe₂. The observation that electron-doped superconductivity does not behave as an Ising-like superconductor suggests that the role of WSe₂ in stabilizing superconductivity in BBG may not be solely attributed to Ising SOC. These observations provide substantial constraints on theoretical models for understanding the mechanism of superconductivity in crystalline graphene systems.

Reference

- 1. Cao, Y. *et al.* Unconventional superconductivity in magic-angle graphene superlattices. *Nature* **556**, 43-50 (2018).
- 2. Yankowitz, M. *et al.* Tuning superconductivity in twisted bilayer graphene. *Science* **363**, 1059-1064 (2019).
- 3. Lu, X. B. *et al.* Superconductors, orbital magnets and correlated states in magic-angle bilayer graphene. *Nature* **574**, 653-657 (2019).
- 4. Saito, Y., Ge, J., Watanabe, K., Taniguchi, T. & Young, A. F. Independent superconductors and correlated insulators in twisted bilayer graphene. *Nat. Phys.* 16, 926-930 (2020).
- 5. Stepanov, P. *et al.* Untying the insulating and superconducting orders in magic-angle graphene. *Nature* **583**, 375-378 (2020).
- 6. Liu, X. *et al.* Tuning electron correlation in magic-angle twisted bilayer graphene using Coulomb screening. *Science* **371**, 1261-1265 (2021).
- Park, J. M., Cao, Y., Watanabe, K., Taniguchi, T. & Jarillo-Herrero, P. Tunable strongly coupled superconductivity in magic-angle twisted trilayer graphene. *Nature* 590, 249-255 (2021).
- 8. Hao, Z. *et al.* Electric field–tunable superconductivity in alternating-twist magic-angle trilayer graphene. *Science* **371**, 1133-1138 (2021).
- 9. Cao, Y., Park, J. M., Watanabe, K., Taniguchi, T. & Jarillo-Herrero, P. Pauli-limit violation and re-entrant superconductivity in moiré graphene. *Nature* **595**, 526-531 (2021).
- 10. Liu, X., Zhang, N. J., Watanabe, K., Taniguchi, T. & Li, J. I. A. Isospin order in superconducting magic-angle twisted trilayer graphene. *Nat. Phys.* 18, 522-527 (2022).
- 11. Zhang, Y. *et al.* Promotion of superconductivity in magic-angle graphene multilayers. *Science* **377**, 1538-1543 (2022).
- 12. Park, J. M. *et al.* Robust superconductivity in magic-angle multilayer graphene family. *Nat. Mater.* **21**, 877-883 (2022).

- 13. Arora, H. S. *et al.* Superconductivity in metallic twisted bilayer graphene stabilized by WSe₂. *Nature* **583**, 379-384 (2020).
- Su, R., Kuiri, M., Watanabe, K., Taniguchi, T. & Folk, J. A. Superconductivity in twisted double bilayer graphene stabilized by WSe₂. *Nat. Mater.* 22, 1332 - 1337 (2023).
- 15. Oh, M. et al. Evidence for unconventional superconductivity in twisted bilayer graphene. Nature 600, 240-245 (2021).
- 16. Kim, H. et al. Evidence for unconventional superconductivity in twisted trilayer graphene. Nature 606, 494-500 (2022).
- 17. Tian, H. *et al.* Evidence for Dirac flat band superconductivity enabled by quantum geometry. *Nature* **614**, 440-444 (2023).
- 18. Zhou, H., Xie, T., Taniguchi, T., Watanabe, K. & Young, A. F. Superconductivity in rhombohedral trilayer graphene. *Nature* **598**, 434-438 (2021).
- 19. Zhou, H. *et al.* Isospin magnetism and spin-polarized superconductivity in Bernal bilayer graphene. *Science* **375**, 774-778 (2022).
- 20. Zhang, Y. *et al.* Enhanced superconductivity in spin-orbit proximitized bilayer graphene. *Nature* **613**, 268-273 (2023).
- 21. Holleis, L. *et al.* Ising Superconductivity and Nematicity in Bernal Bilayer Graphene with Strong Spin Orbit Coupling. Preprint at https://arxiv.org/abs/2303.00742 (2023).
- 22. Gmitra, M. & Fabian, J. Graphene on transition-metal dichalcogenides: A platform for proximity spin-orbit physics and optospintronics. *Phys. Rev. B* **92**, 155403 (2015).
- 23. Gmitra, M. & Fabian, J. Proximity Effects in Bilayer Graphene on Monolayer WSe₂: Field-Effect Spin Valley Locking, Spin-Orbit Valve, and Spin Transistor. *Phys. Rev. Lett.* **119**, 146401 (2017).
- 24. Khoo, J. Y., Morpurgo, A. F. & Levitov, L. S. On-Demand Spin-Orbit Interaction from Which-Layer Tunability in Bilayer Graphene. *Nano Lett.* **17 11**, 7003-7008 (2017).
- 25. Li, Y. & Koshino, M. Twist-angle dependence of the proximity spin-orbit coupling in graphene on transition-metal dichalcogenides. *Phys. Rev. B* **99**, 075438 (2019).
- 26. Avsar, A. et al. Spin-orbit proximity effect in graphene. Nat. Commun. 5, 4875 (2014).
- 27. Wang, Z. *et al.* Origin and Magnitude of 'Designer' Spin-Orbit Interaction in Graphene on Semiconducting Transition Metal Dichalcogenides. *Phys. Rev. X* **6**, 041020 (2016).
- 28. Yang, B. W. *et al.* Tunable spin-orbit coupling and symmetry-protected edge states in graphene/WS₂. *2D Mater.* **3**, 031012 (2016).
- 29. Wakamura, T. et al. Strong anisotropic spin-orbit interaction induced in graphene by monolayer WS₂. *Phys. Rev. Lett.* **120**, 106802 (2018).
- Wang, D. *et al.* Quantum Hall Effect Measurement of Spin-Orbit Coupling Strengths in Ultraclean Bilayer Graphene/WSe₂ Heterostructures. *Nano Lett.* 19, 7028-7034 (2019).
- 31. Island, J. O. et al. Spin-orbit-driven band inversion in bilayer graphene by the van der

Waals proximity effect. Nature 571, 85-89 (2019).

- 32. Lin, J. X. *et al.* Spin-orbit-driven ferromagnetism at half moiré filling in magic-angle twisted bilayer graphene. *Science* **375**, 437-441 (2022).
- 33. Han, T. *et al.* Large Quantum Anomalous Hall Effect in Spin-Orbit Proximitized Rhombohedral Graphene. Preprint at https://arxiv.org/abs/2310.17483 (2023).
- 34. Sha, Y. *et al.* Observation of Chern insulator in crystalline ABCA-tetralayer graphene with spin-orbit coupling. *Science* **384**, 414-419 (2024).
- 35. Balents, L., Dean, C. R., Efetov, D. K. & Young A. F. Superconductivity and strong correlations in moiré flat bands. *Nat. Phys.* 16, 725-733 (2020).
- 36. Törmä, P., Peotta, S. & Bernevig, B. A. Superconductivity, superfluidity and quantum geometry in twisted multilayer systems. *Nat. Rev. Phys.* 4, 528-542 (2022).
- 37. Pantaleón, P. A. *et al.* Superconductivity and correlated phases in non-twisted bilayer and trilayer graphene. *Nat. Rev. Phys.* **5**, 304-315 (2023).
- 38. Zhou, H. *et al.* Half- and quarter-metals in rhombohedral trilayer graphene. *Nature* **598**, 429-433 (2021).
- 39. de la Barrera, S. C. *et al.* Cascade of isospin phase transitions in Bernal-stacked bilayer graphene at zero magnetic field. *Nat. Phys.* **18**, 771-775 (2022).
- 40. Seiler, A. M. *et al.* Quantum cascade of correlated phases in trigonally warped bilayer graphene. *Nature* **608**, 298-302 (2022).
- 41. Lin, J. X. *et al.* Spontaneous momentum polarization and diodicity in Bernal bilayer graphene. Preprint at https://arxiv.org/abs/2302.04261 (2023).
- 42. Liu, K. et al. Spontaneous broken-symmetry insulator and metals in tetralayer rhombohedral graphene. Nat. Nanotechnol. (2023).
- 43. Han, T. *et al.* Correlated insulator and Chern insulators in pentalayer rhombohedralstacked graphene. *Nat. Nanotechnol.* (2023).
- 44. Han, T. *et al.* Orbital multiferroicity in pentalayer rhombohedral graphene. *Nature* **623**, 41-47 (2023).
- 45. Lu, Z. et al. Fractional Quantum Anomalous Hall Effect in a Graphene Moire Superlattice. Nature 626, 759-764 (2024).
- 46. McCann, E. & Koshino, M. The electronic properties of bilayer graphene. *Rep. Prog. Phys.* **76**, 056503 (2013).
- Lu, J. M. *et al.* Evidence for two-dimensional Ising superconductivity in gated MoS₂. *Science* 350, 1353-1357 (2015).
- 48. Saito, Y. *et al.* Superconductivity protected by spin-valley locking in ion-gated MoS₂. *Nat. Phys.* **12**, 144–149 (2016).
- 49. Xi, X. *et al.* Ising pairing in superconducting NbSe₂ atomic layers. *Nat. Phys.* **12**, 139–143 (2016).

Methods

Device Fabrication

The BBG/WSe₂ device has a dual graphite gate geometry and is assembled by using the standard dry-transfer technique⁵⁰. A poly (bisphenol A carbonate)/polydimethylsiloxane stamp mounted on a glass slide is used to pick up each layer. The stacking sequence from top to bottom consists of the following layers: graphite as the top gate electrode, top hexagonal boron nitride (hBN) as the top dielectric, monolayer WSe₂ (Commercial source, HQ graphene), graphite as the contact electrodes, BBG, bottom hBN as the bottom dielectric, and graphite as the bottom gate electrode. The entire structure is released onto a Si/SiO₂ substrate at 180 °C. The stack is then shaped into a Hall-bar geometry using reactive ion etching with CHF₃/O₂, and Cr/Au (2/100nm) is deposited as the metal edge contacts by electron beam evaporation. The device image is shown in Extended Data Fig. 11.

Transport Measurements

The dual gate geometry allows us to independently tune the carrier density $\left(n = \frac{c_t V_t + c_b V_b}{e} + n_0\right)$ and the vertical electric displacement field $\left(D = \frac{c_t V_t - c_b V_b}{2\varepsilon_0} + D_0\right)$ in BBG by applying top gate voltage V_t and back gate voltage V_b . Here, ε_0 , c_t , c_b , n_0 and D_0 denote the vacuum permittivity, geometric capacitance of the top gate, geometric capacitance of the back gate, intrinsic doping and the build-in electric field, respectively.

Electrical transport measurements were performed in two dilution refrigerators. One is a top-loading dilution refrigerator (Oxford TLM, nominal base temperature about 15 mK) with 18 T superconducting magnet. The sample is immersed in the He³-He⁴ mixtures during the measurements. Each fridge line has a sliver epoxy filter and a RC- filter (consisting of a 470 Ω resistor and a 100-pF capacitor) at low temperature. Another one is a bottom-loading dilution refrigerator (Oxford Triton, nominal base temperature about 10 mK) with a vector superconducting magnet of 9-1-1 T, and the in-plane magnetic field dependence measurement is performed in this dilution refrigerator. For the 9-1-1 T dilution refrigerator, each fridge line has a π -filter at room temperature, consisting of a 1 k Ω resistor and a 10 mH inductor; and a RC-filter at low-temperature, consisting of a 1 k Ω resistor and a 1nF capacitor. We performed the electrical transport measurements by using the standard low-frequency (< 23 Hz) lock-in (SR830 and SR860) techniques. The bias current is limited within 3 nA, to avoid sample heating, and avoid disturbing the fragile states. Voltage pre-amplifier with 100 M Ω impedance were used to improve the signal-tonoise ratio.

It is worth noting that, on the hole-doped side, we did not observe the in-plane magnetic field-induced superconductivity ($T_c \sim 30 \text{ mK}$) at D < 0 (reported in Ref. 19) and the SC1 phase ($T_c \sim 40 \text{ mK}$) at D > 0 reported in Ref. 21, presumably limited by the sample quality or effective electron temperature of our dilution refrigerators.

Superconducting coherence length, mean free path, and critical current density

The Ginzburg-Landau superconducting coherence length ξ can be estimated from the relation⁵¹ $\xi = \sqrt{\Phi_0/(2\pi B_{c\perp})}$, where $\Phi_0 = h/2e$ is the superconducting flux quantum, and $B_{c\perp}$ is the critical perpendicular magnetic field at zero temperature. The measured $B_{c\perp}$ of both electron- and hole-doped superconductivity in our device at ~20 mK (<< T_c) ranges from ~ 5 mT to 15 mT (Extended Data Fig. 12), yielding $\xi \approx 150$ nm – 250 nm. This is comparable to values reported in previous studies of crystalline graphene systems¹⁸⁻²¹.

The mean free path $l_{\rm m}$ can be estimated¹⁹ based on the onset magnetic field B_{onset} of quantum oscillations by $l_{\rm m} \sim 2\pi k_F l_B^2$, where k_F is the Fermi wave vector, and l_B is the magnetic length at B_{onset} . The k_F of BBG can be estimated by $k_F \sim \sqrt{\pi |n|}$. The carrier density range of the observed electron- and hole doped superconductivity is around $|n| = 0.5 \cdot 1.2 \times 10^{12}$ cm⁻², and the B_{onset} is about 0.2-0.3 T, giving the $l_{\rm m}$ about 2 µm to 5 µm. Overall, the $\xi/l_{\rm m}$ ratio are smaller than 0.1 in BBG/WSe₂ system, suggesting that both the electron-doped and hole-doped superconductivity are in the clean limit.

Based on the measured critical current I_c (Fig. 1g, 1j) and Hall bar width (~1.5 µm, see Extended Data Fig. 11), we estimate that the critical current density J_c of the hole-doped superconductivity in our device ranges from ~40 nA/µm to ~110 nA/µm, with T_c ranging from ~150 mK to ~450 mK. These values are significantly larger than the previously reported J_c values of ~2-5 nA/µm (with T_c ~200-300 mK) in hole-doped BBG/WSe₂ devices^{20,21}. We found the J_c of the electron-doped superconductivity is smaller, ranging from ~15 nA/µm to ~40 nA/µm (with T_c ~150 mK to ~300 mK) in our device.

Normalized FFT frequency fv

 f_v is defined as $f_v = f_{FFT} \times e/nh$, where f_{FFT} is the quantum oscillation frequency (in tesla) of $R_{xx}(B_\perp)$ derived by FFT, with *n*, *h* and *e* denoting the total carrier density, Planck's constant and electron charge, respectively. f_v represents the fraction of the total Luttinger volume enclosed by a given cyclotron orbit. The sum of $f_v^{(i)}$ with degeneracy N_i should be normalized, namely $\sum_i s_i N_i f_v^{(i)} = 1$, where s_i is +1 (-1) when the *i*th cyclotron orbit encloses an electron (hole) pocket for electron doping (the rule is opposite for hole doping).

Theoretical superconducting mechanisms for BBG

We present a brief review about theoretical superconducting mechanisms for BBG. The proposed pairing mechanisms include electron-phonon coupling⁵²⁻⁵⁵, electron-electron interactions⁵⁶⁻⁶⁰, electronic collective fluctuations in quantum critical models⁶¹⁻⁶², etc. The enhancement of superconductivity in BBG coupled to WSe₂ has often been attributed to the proximity-induced Ising spin-orbit coupling either through the electron-electron interaction mechanism⁵⁶⁻⁵⁸ or by suppressing spin fluctuations⁶³. In addition, virtual

tunneling between WSe₂ and BBG has also been proposed to enhance superconductivity⁵⁴. A thorough review of superconductivity and correlated phases in non-twisted graphene systems can be found in Ref. 37.

Calculations

We use a continuum *k.p* model to describe the low-energy band structure of BBG,

$$H_{0} = \sum_{\tau=\pm} \sum_{k} \psi_{\tau}^{\dagger}(k) [h_{0,\tau}(k)s_{0}]\psi_{\tau}(k),$$
$$h_{0,\tau}(k) = \begin{pmatrix} \frac{U}{2} & v_{0}\Pi^{\dagger} & -v_{4}\Pi^{\dagger} & -v_{3}\Pi \\ v_{0}\Pi & \Delta + \frac{U}{2} & \gamma_{1} & -v_{4}\Pi^{\dagger} \\ -v_{4}\Pi & \gamma_{1} & \Delta - \frac{U}{2} & v_{0}\Pi^{\dagger} \\ -v_{3}\Pi^{\dagger} & -v_{4}\Pi & v_{0}\Pi & -\frac{U}{2} \end{pmatrix}$$

where $\tau = \pm 1$ is the valley index, s_0 is the identity matrix in the spin space, and $h_{0,\tau}(\mathbf{k})$ is a 4 × 4 matrix expressed in the space (A1, B1, A2, B2) with A1 (A2) and B1 (B2) are sublattices in bottom (top) layers. In $h_{0,\tau}(\mathbf{k})$, $\Pi = (\tau k_x + i k_y)$, U is the interlayer potential difference between the top and bottom layers generated by an external out-ofplane displacement field, and the velocities can be parametrized as $v_i = \sqrt{3}a_0\gamma_i/2$ for i =0, 3, 4 with $a_0 = 0.246$ nm being the lattice constant of monolayer graphene. We take the following parameter values from Ref. [66], $\gamma_0 = 2.61 \text{ eV}$, $\gamma_1 = 361 \text{ meV}$, $\gamma_3 = 283 \text{ meV}$, $\gamma_4 = 138 \text{ meV}$, and $\Delta = 15 \text{ meV}$. The potential U is related to the displacement field D by U = eDd_0/ϵ , where e is the elementary charge, d_0 is the interlayer distance of BBG, and ϵ is the dielectric constant. Given the uncertainties in the value of ϵ , we use the parameter U in the calculation.

A monolayer WSe₂ adjacent to the bilayer graphene generates spin-orbit coupling (SOC) terms given by,

$$H_{\text{SOC}} = \sum_{\tau=\pm} \sum_{\boldsymbol{k}} \psi_{\tau}^{\dagger}(\boldsymbol{k}) [h_{\text{SOC},\tau}(\boldsymbol{k})] \psi_{\tau}(\boldsymbol{k}),$$
$$h_{\text{SOC},\tau}(\boldsymbol{k}) = \left[\frac{\lambda_{I}}{2} \tau s_{z} + \frac{\lambda_{R}}{2} (\tau \sigma_{x} s_{y} - \sigma_{y} s_{x})\right] \frac{l_{0} - l_{z}}{2}$$

where the Pauli matrices $s_{x,y,z}$ and $\sigma_{x,y}$ act, respectively, on the spin and sublattice space. The operator $\frac{l_0 - l_z}{2}$ projects the SOC term onto the top layer graphene, where l_0 and l_z are, respectively, identity and Pauli z matrix in the layer space. The parameters λ_I and λ_R quantify the strength of the Ising and Rashba SOC. In our theoretical calculation, we only keep the Ising SOC term for simplicity, and take $\lambda_I = 2$ meV and $\lambda_R = 0$ meV. Detailed effects of Rashba SOC are left for future study. The single-particle band structure and DOS shown in Fig. 1b and Extended Data Fig. 3b, 3c are calculated using the Hamiltonian $H_1 = H_0 + H_{SOC}$.

We consider Coulomb interaction described by:

$$H_{C} = \frac{1}{2A} \sum_{\boldsymbol{k}, \boldsymbol{k}', \boldsymbol{q}, \alpha, \beta} V(\boldsymbol{q}) \psi_{\alpha}^{\dagger}(\boldsymbol{k}) \psi_{\beta}^{\dagger}(\boldsymbol{k}') \psi_{\beta}(\boldsymbol{k}' - \boldsymbol{q}) \psi_{\alpha}(\boldsymbol{k} + \boldsymbol{q}),$$

where α and β represent layer, sublattice, spin and valley indices, and *A* is area of the system. We use the gate-screened Coulomb potential $V(q) = \frac{2\pi e^2}{\epsilon_r |q|} \tanh |q|d$, where ϵ_r is a phenomenological dielectric constant and *d* is the gate-to-sample distance. Here we take ϵ_r as a phenomenological parameter taking into account both environmental screening from hBN and internal metallic screening. We use Hartree-Fock approximation to study the full Hamiltonian $H = H_1 + H_C = H_0 + H_{SOC} + H_C$, and compare mean-field energies of competing states, including symmetric states and symmetry-breaking states (spin and/or valley polarized states are examined). The theoretical results for electron doping are illustrated in Extended Data Fig. 6. In the calculation, we use $\epsilon_r = 20$ and d = 20 nm. Related theoretical studies can be found, for example, in Refs. 64 and 65.

Band alignment between BBG and monolayer WSe₂

As illustrated in Fig. 1b, the charge neutral point of BBG is deep within the monolayer WSe₂ semiconducting band gap (~1.8 eV). We now argue that the WSe₂ layer is not doped for electric field within $D=\pm 1.65$ V/nm by considering a simple model. In the presence of an electric field, the energies of valence band maximum (VBM) and conduction band minimum (CBM) in BBG are (neglecting the tiny Ising SOC), respectively, -|U|/2 and +|U|/2, where $U = eDd_0/\epsilon$. The energies of VBM and CBM in WSe₂ are respectively, $E_v - U_1$ and $E_c - U_1$. Here E_v (E_c) is the energy of WSe₂ VBM (CBM) measured relative to the BBG charge neutrality point in the absence of the electric field. Based on the experimentally determined band offsets in WSe₂ and graphene systems⁶⁷⁻⁶⁹, we estimate that $E_v = -0.6$ eV and $E_c = 1.2$ eV. The energy shift U_1 due to the applied electric field is given by $U_1 = eD(d_0/2 + d_1)/\epsilon$, where d_1 is the interlayer distance between WSe₂ and its adjacent graphene layer. The energy offset in VBM (CBM) between BBG and WSe₂ is given, respectively, by,

$$\delta E_{v} = -\frac{|U|}{2} - (E_{v} - U_{1}) = \begin{cases} |E_{v}| + \frac{e|D|d_{1}}{\epsilon}, & D > 0\\ |E_{v}| - \frac{e|D|(d_{0} + d_{1})}{\epsilon}, & D < 0 \end{cases};$$

$$\delta E_{c} = (E_{c} - U_{1}) - \frac{|U|}{2} = \begin{cases} |E_{c}| - \frac{e|D|(d_{0} + d_{1})}{\epsilon}, & D > 0\\ |E_{c}| + \frac{e|D|d_{1}}{\epsilon}, & D < 0 \end{cases}$$

By taking |D| to be the upper limit of 1.65 V/nm, $\epsilon \approx 4$, $d_0 \approx 0.34$ nm, and $d_1 \approx 0.5$ nm, we find that all the above band offsets remain at least larger than 0.25 eV. Therefore, we conclude that the WSe₂ layer is not doped for electric field within $D=\pm 1.65$ V/nm. Moreover, the relevant band offsets increase with increasing |D| for the two regimes: (1) D > 0 and hole doping to the valence band of BBG; (2) D < 0 and electron doping to the conduction band of BBG. These two regimes, in which superconductivity has been observed, are the main focus of our work. In experiment, we also do not find any signature of carrier doped into the WSe₂ layer, consistent with the above analysis.

- 50. Wang, L. et al. One-dimensional electrical contact to a two-dimensional material. *Science* **342**, 614–617 (2013).
- 51. Tinkham, M. *Introduction to Superconductivity*. 2nd edition (McGraw-Hill, New York, 1975).
- 52. Chou, Y.-Z., Wu, F., Sau, J. & Sarma, S. Acoustic-phonon-mediated superconductivity in Bernal bilayer graphene. *Phys. Rev. B* 105, L100503 (2022).
- 53. Chou, Y.-Z., Wu, F., Sau, J. D. & Das Sarma, S. Acoustic-phonon-mediated superconductivity in moiréless graphene multilayers. *Phys. Rev. B* **106**, 024507 (2022).
- 54. Chou, Y.-Z., Wu, F. & Das Sarma, S. Enhanced superconductivity through virtual tunneling in Bernal bilayer graphene coupled to WSe₂. *Phys. Rev. B* **106**, L180502 (2022).
- 55. Boström, E. V. *et al.* Phonon-mediated unconventional *s* and *f*-wave pairing superconductivity in rhombohedral stacked multilayer graphene. Preprint at https://arxiv.org/abs/2311.02494 (2023).
- 56. Jimeno-Pozo, A., Sainz-Cruz, H., Cea, T., Pantaleón, P. A. & Guinea, F. Superconductivity from electronic interactions and spin-orbit enhancement in bilayer and trilayer graphene. *Phys. Rev. B* **107**, L161106 (2023).
- 57. Wagner, G., Kwan, Y., Bultinck, N., Simon, S. & Parameswaran, S. Superconductivity from repulsive interactions in Bernal-stacked bilayer graphene. Preprint at https://arxiv.org/abs/2302.00682 (2023).
- 58. Li, Z. et al. Charge fluctuations, phonons, and superconductivity in multilayer graphene. *Phys. Rev. B* 108, 045404 (2023).
- 59. Cea, T. Superconductivity induced by the intervalley Coulomb scattering in a few layers of graphene. *Phys. Rev. B* 107, L041111 (2023).
- 60. Szabó, A. L. & Roy, B. Competing orders and cascade of degeneracy lifting in doped

Bernal bilayer graphene. Phys. Rev. B 105, L201107 (2022).

- 61. Dong, Z., Chubukov, A. V. & Levitov, L. Transformer spin-triplet superconductivity at the onset of isospin order in bilayer graphene. *Phys. Rev. B* **107**, 174512 (2023).
- 62. Dong, Z., Levitov, L. & Chubukov, A. V. Superconductivity near spin and valley orders in graphene multilayers. *Phys. Rev. B* 108, 134503 (2023).
- 63. Curtis, J. B. *et al.* Stabilizing Fluctuating Spin-Triplet Superconductivity in Graphene via Induced Spin-Orbit Coupling. *Phys. Rev. Lett.* **130**, 196001 (2023).
- 64. Xie, M. & Das Sarma, S. Flavor symmetry breaking in spin-orbit coupled bilayer graphene. *Phys. Rev. B* 107, L201119 (2023).
- 65. Dong, Z., Davydova, M., Ogunnaike, O. & Levitov, L. Isospin- and momentumpolarized orders in bilayer graphene. *Phys. Rev. B* 107, 075108 (2023).
- 66. Jung, J. & MacDonald, A. H. Accurate tight-binding models for the π bands of bilayer graphene. *Phys. Rev. B* 89, 035405 (2014).
- 67. Wilson, N. R. *et al.* Determination of band offsets, hybridization, and exciton binding in 2D semiconductor heterostructures. *Sci. Adv.* 3, e1601832 (2017).
- 68. Xu, Y. *et al.* Creation of moiré bands in a monolayer semiconductor by spatially periodic dielectric screening. *Nat. Mater.* 20, 645-649 (2021).
- 69. Yu, Y. J. *et al.* Tuning the Graphene Work Function by Electric Field Effect. *Nano. Lett.* 9, 3430-3434 (2009).

Acknowledgement

We thank Yangzhi Chou, Jianpeng Liu, Yang Zhang, and Fanqi Yuan for helpful discussions. This work is supported by the National Key R&D Program of China (No. 2022YFA1405400, 2022YFA1402702, 2022YFA1402404, 2019YFA0308600, 2022YFA1402401, 2020YFA0309000), the National Natural Science Foundation of China (No. 12350403, 12174249, 92265102, 12374045), the Innovation Program for Quantum Science and Technology (Grants No. 2021ZD0302600 and No. 2021ZD0302500), the Natural Science Foundation of Shanghai (No. 22ZR1430900), the Shanghai Jiao Tong University 2030 Initiative Program. X.L. acknowledges the Pujiang Talent Program 22PJ1406700. T.L. acknowledges the Yangyang Development Fund. K.W. and T.T. acknowledge support from the JSPS KAKENHI (Grants No. 21H05233 and No. 23H02052) and World Premier International Research Center Initiative (WPI), MEXT, Japan. This work was supported by the Synergetic Extreme Condition User Facility (SECUF).

Author contributions

T.L. and X.L. designed the experiment. C.L. and F.X. fabricated the devices. C.L., F.X. and J.L. performed the measurements with the assistance of G.L. and B. T.

X.L., C.L., T.L. and F.W. analyzed the data. B. L. and F. W. performed theoretical studies. K.W. and T.T. grew the bulk hBN crystals. T.L., X.L., and F.W. wrote the manuscript. All authors discussed the results and commented on the manuscript.

Competing interests

The authors declare no competing financial interests.

Main Figures



17

Fig. 1. Phase diagram, electron- and hole-doped superconductivity of BBG/WSe₂. a, Schematic of the dual-gated BBG/WSe₂ device. **b**, Schematic band alignment of monolayer WSe₂ and BBG at D = 0V/nm. The charge neutral point of BBG is deep within the WSe₂ semiconducting band gap. c, Calculated single-particle band structure near the K and K' points of the Brillouin zone for interlayer potential difference $U = \pm 100$ meV, which roughly corresponds to the displacement field $D \approx \pm 1$ V/nm. At positive (negative) D, hole (electron) wavefunctions concentrate at the top layer of BBG, so the WSe_2 induced SOC is much more prominent in the valence (conduction) band. d, R_{xx} -D-n map measured at T = 20 mK, covering both the electron-doped ($0 \le n \le 1.0 \times 10^{12}$ cm⁻², -1.65 V/nm $\le D \le 1.60$ V/nm) and hole-doped (-1.5×10¹² cm⁻² < n < 0, -1.55 V/nm < D < 1.55 V/nm) regions. e, Experimental phase diagram determined based on d and FFT analysis of quantum oscillations. We use the R_{xx} features in d as the phase boundaries. The possible Fermi surface structure (shown by schematics) for each phase is inferred by the FFT analysis of quantum oscillations, assuming that spin-valley flavors are not mixed. The superconducting region is marked by dashed lines. f, i, dV_{xx}/dI_{dc} versus I_{dc} of the hole- (f) and electron-doped superconductivity (i) at various D. g, j, I_c (upper panel) and T_c (lower panel) versus D of the hole- (g) and electron-doped superconductivity (j). h, k, Temperature dependence of R_{xx} versus n on the hole-doped side at D = 1.1 V/nm (h) and on the electron-doped side at D = -1.64 V/nm (k). The insets show the R_{xx} versus T curves at the optimal doping, where T_c reaches its highest value.



Fig. 2. Fermi surface analysis of the hole-doped superconductivity. **a**, **b**, R_{xx} versus *n* and B_{\perp} at D = 1.1 V/nm (**a**) and 1.5 V/nm (**b**) on the hole-doped side. **c**, **d**, FFT of R_{xx} ($1/B_{\perp}$) versus *n* and f_v at D = 1.1 V/nm (**c**) and 1.5 V/nm (**d**) on the hole-doped side. The FFT analysis in **c** and **d** is performed based on the R_{xx} data within 0.2 T < B_{\perp} < 1 T, respectively. The schematic Fermi surface structures for different phases are also shown in **c** and **d**. The frequency peaks of the FFT for different phases are highlighted by red arrows. **e**, **f**, R_{xx} versus *n* at B = 0 T measured at D = 1.1 V/nm (**e**) and 1.5 V/nm (**f**) on the hole-doped side. At D = 1.1 V/nm, a superconducting state is observed within the PIP₂ phase near the trigonal warping phase with the Ising SOC-induced spin splitting.



Fig. 3. Fermi surface analysis of the electron-doped superconductivity. **a**, **b**, R_{xx} versus *n* and B_{\perp} at D = 1.55 V/nm (**a**) and -1.55 V/nm (**b**) on the electron-doped side. **c**, **d**, FFT of R_{xx} ($1/B_{\perp}$) versus *n* and f_v at D = 1.55 V/nm (**c**) and -1.55 V/nm (**d**) on the electron-doped side. The FFT analysis in **c** and **d** is performed based on the R_{xx} data within 0.2 T $< B_{\perp} < 1$ T in **a** and **b**, respectively. The schematic Fermi surface structures for the different phases are also shown in **c** and **d**. **e**, **f**, R_{xx} versus *n* at B = 0 T at D = 1.55 V/nm (**e**) and -1.55 V/nm (**f**) on the electron-doped side. Electron-doped superconductivity can only be observed at negative *D*.



Fig. 4. The in-plane magnetic field dependence of both hole-doped and electron-doped superconductivity. **a**, **b**, R_{xx} as a function of T and n at D = 0.96 V/nm for the hole-doped superconducting dome (**a**), and D = -1.64 V/nm for the electron-doped superconducting dome (**b**), respectively. **c**, **d**, R_{xx} as a function of B_{\perp} and n at D = 0.96 V/nm for the hole-doped superconducting dome (**c**), and D = -1.64 V/nm for the electron-doped superconducting dome (**d**), respectively. Both the superconducting T_c and $B_{c\perp}$ are similar at these two specific D values. **e**, **f**, R_{xx} as a function of B_{\parallel} and n at D = 0.96 V/nm (**e**) and D = -1.64 V/nm (**f**), respectively. The hole-doped superconducting dome at D = 0.96 V/nm (**e**) and D = -1.64 V/nm (**f**), respectively. The hole-doped superconducting dome at D = -1.64 V/nm is completely suppressed under a small $B_{\parallel} \sim 0.2$ T. **g**, **h**, Pauli violation ratio $B_{c\parallel}^0/B_p$ versus n at D = 0.96 V/nm (**g**) and D = -1.64 V/nm (**h**), respectively. The hole-doped superconductivity violates the Pauli limit, while electron-doped superconductivity obeys the Pauli limit. Moreover, $B_{c\parallel}^0/B_p$ in both hole- and electron-doped superconductivity exhibit density dependent behaviors.

Extended Data Figures



Extended Data Fig. 1. Estimate the strength of Ising SOC from the transition at quantum hall state |v| = 3. a-e, R_{xx} as a function of D and Landau level filling factors v at $B_{\perp} = 2$ T (a), $B_{\perp} = 4$ T (b), $B_{\perp} = 5$ T (c), $B_{\perp} = 6$ T (d) and $B_{\perp} = 8$ T (e). The blue and green arrows in each panel mark the orbital transitions of quantum hall state |v| = 3. f, The D extracted from the transition at |v| = 3 in a-e as a function of B_{\perp} , and the red and black lines are fits to the data, respectively. The strength of Ising SOC could be estimated from the crossing point of the two fitting lines where the out-of-plane Zeeman energy E_z compensates the energy split λ_I due to Ising SOC^{20,21,31}. According to $\lambda_I = 2E_z = 2g\mu_B B_{SOC}$, where B_{SOC} is the perpendicular magnetic field where the two fitting lines intersect, the strength of Ising SOC λ_I in our device is estimated to be about 1.7 meV.



Extended Data Fig. 2. Estimation of T_{BKT} , density dependent T_c and I_c at various D. a, c, dV_{xx}/dI_{dc} at the optimal doping as a function of I_{dc} measured at various temperatures at D = +1.1 V/nm (a) and D = -1.64 V/nm (c) for the hole- and electron-doped superconductivity, respectively. An ac modulation current of 2 nA is used for the differential resistance measurements. b, d, The nonlinear voltage-current ($V_{dc}-I_{dc}$) curves of **a** and **c**. The dashed line is a power law fit of $V \propto I^3$, yielding $T_{BKT} = 400$ mK (b) and $T_{BKT} = 210$ mK (d) for the hole-doped and electron-doped superconductivity, respectively. **e**-g, R_{xx} as a function of *n* and *T* for hole-doped superconducting domes at D = 0.96 V/nm (e), D = 1.1 V/nm (f) and D = 1.27 V/nm (g), respectively. **h**, R_{xx} as a function of *n* and *T* for superconducting domes at D = 0.96 V/nm, (j) D = 1.1 V/nm, (k) D = 1.27 V/nm and (l) D = -1.47 V/nm, respectively. A competing resistive phase intersecting the hole-doped superconducting domes at D = 0.96 V/nm, (j) D = 1.1 V/nm, (k) D = 1.27 V/nm and (l) D = -1.47 V/nm, respectively. A competing resistive phase intersecting the hole-doped superconducting domes at D = 0.96 V/nm, (j) D = 1.1 V/nm, (k) D = 1.27 V/nm and (l) D = -1.47 V/nm, respectively. A competing resistive phase intersecting the hole-doped superconducting dome reported previously²⁰ is evident at D = 0.96 V/nm and eventually diminishes with further increasing D. The data shown in **i**-l and the data shown in **e**-**h** were taken during separate rounds of measurements conducted in different dilution refrigerators. We found that the width of the superconducting dome in density can vary slightly between different rounds of measurements.



Extended Data Fig. 3. DOS calculation. a-c Total density of state (DOS) in BBG as a function of doping density *n* without (**a**) and with (**b-c**) the Ising SOC term for different values of the layer potential difference *U*. At positive (negative) *U*, hole wavefunctions (electron wavefunctions) concentrate at the top graphene layer which is closer to the WSe₂ layer, so the proximity-induced Ising SOC is only notable in the VB (CB).



Extended Data Fig. 4. Fermi surface analysis of the hole-doped BBG/WSe₂ at negative *D* fields. a, b, R_{xx} versus *n* and B_{\perp} at D = -1.1 V/nm (a) and -1.5 V/nm (b) on the hole-doping side. c, d, FFT of R_{xx} $(1/B_{\perp})$ versus *n* and f_v at D = -1.1 V/nm (c) and -1.5 V/nm (d) on the hole-doping side. The FFT analysis in c and d is performed based on the R_{xx} data within 0.2 T $< B_{\perp} < 1$ T in a and b, respectively. No SOC induced FFT peak splitting can be identified at negative *D*-fields on the hole-doping side. The schematic Fermi surface structures for different phases are also shown in c and d. e, f, R_{xx} versus *n* at B = 0 T at D= -1.1 V/nm (e) and -1.5 V/nm (f) on the hole-doping side. In the PIP₂ phase at D = -1.1 V/nm, instead of superconductivity, a resistive state emerges.



Extended Data Fig. 5. Fermi surface analysis of the hole-doped BBG/WSe₂ at D = 1.19 V/nm. a, R_{xx} -D-n map of hole-doped BBG/WSe₂ within a narrower n, D range. Apart from the superconducting region described in the main text, another region with reduced R_{xx} emerges at lower hole doping, within D-field range ~ 1.1 - 1.3 V/nm (marked by the green arrow). **b**, Temperature dependence of R_{xx} versus *n* on the hole-doping side at D = 1.19 V/nm. The additional resistance dip at ~ 0.56×10^{12} cm⁻² can be observed. Such resistance dip may indicate the developing of another superconducting dome, which may need further studies in higher quality devices or at lower temperatures. c, R_{xx} versus n and B_{\perp} at D = 1.19 V/nm on the hole-doping side. **d**, FFT of R_{xx} (1/ B_{\perp}) versus *n* and f_{v} at D = 1.19V/nm on the holedoping side. The FFT analysis is performed based on the R_{xx} data within 0.2 T $\leq B_{\perp} \leq 1.2$ T. A spin- and valley-polarized state with $f_v = 1$ emerges at $n \sim -0.4$ to -0.45×10^{12} cm⁻². With increasing hole density, the FFT peak becomes less than 1 and new FFT peaks emerge at very low frequencies. These FFT features indicate a partially isospin polarized phase with one majority and multiple minority Fermi pockets (denoted as PIP_1 phase). Further increasing hole densities, the PIP_1 phase transits into the trigonal warping phase with the Ising SOC-induced spin splitting $(f_v^{(1)} > 1/12 \text{ and } f_v^{(2)} < 1/12)$ until $n \sim 1/12$ -0.75×10^{12} cm⁻². The observed additional R_{xx} dip locates in between of the PIP₁ phase and the trigonal warping phase, as indicated by the green arrow. Similar to D = 1.1 V/nm shown in Fig. 2, the superconducting normal state is within the PIP₂ phase, corresponding to a partial isospin-polarized phase with two major Fermi pockets and multiple minor Fermi pockets. Further increasing hole doping beyond the PIP₂ phase, the system evolves into a state with four annular Fermi surfaces, which is evident by two FFT frequency peaks satisfying $f_v^{(1)} - f_v^{(2)} = 1/4$.



Extended Data Fig. 6. The calculation of Fermi surface structure on the electron-doped side. a-I Theoretically calculated normalized quantum oscillation frequencies f_v as a function of n for different values of U. We first calculate the mean-field ground state (considering both symmetric and symmetrybreaking states) at a given n and U, and then f_v is calculated by the fraction S_i/S , where S_i is area of the ith Fermi pocket and $S = (2\pi)^2 |n|$. The background colors distinguish different patterns of f_v . The results are presented for electron doping (n > 0). U is positive in **a-f** and negative in **g-l**. The Ising SOC coupling strength λ_I is taken to be 2 meV in the calculation. **m-s** Representative Fermi surfaces for different regimes in **l**. Electron densities in **m-s** are $n = (0.1, 0.4, 0.5, 0.8, 1.2, 1.6, 3) \times 10^{12}$ cm⁻², respectively.



Extended Data Fig. 7. Fermi surface analysis at $D = \pm 1.1$ V/nm on the electron-doping side. **a**, **b**, R_{xx} versus *n* and B_{\perp} at D = 1.1 V/nm (**a**) and -1.1 V/nm (**b**) on the electron-doping side. **c**, **d**, FFT of R_{xx} ($1/B_{\perp}$) versus *n* and f_v at D = 1.1 V/nm (**c**) and -1.1 V/nm (**d**) on the electron-doping side. The FFT analysis in **c** and **d** is performed based on the R_{xx} data within 0.1 T $< B_{\perp} < 1$ T in **a** and **b**, respectively. The schematic Fermi surface structures for different phases are also shown in **c** and **d**. Compared to larger *D* values (Fig. 3 and Extended Data Fig. 8), the PIP₁ phase is absent, and the electron density range of the PIP₂ phase become much narrower at $D = \pm 1.1$ V/nm. **e**, **f**, R_{xx} versus *n* at B = 0 T at D = 1.1 V/nm (**f**) on the electron-doping side. Although the flavor-symmetry-breaking phases still exist, the superconductivity is absent at D = -1.1 V/nm.



Extended Data Fig. 8. Fermi surface analysis at $D = \pm 1.64$ V/nm on the electron-doping side. a, b, R_{xx} versus *n* and B_{\perp} at D = 1.64 V/nm (a) and -1.64 V/nm (b) on the electron-doping side. c, d, FFT of R_{xx} ($1/B_{\perp}$) versus *n* and f_v at D = 1.64 V/nm (c) and -1.64 V/nm (d) on the electron-doping side. The FFT analysis in c and d is performed based on the R_{xx} data within 0.2 T $\leq B_{\perp} \leq 1$ T in a and b, respectively. The schematic Fermi surface structures for different phases are also shown in c and d. e, f, R_{xx} versus *n* at B = 0 T at D = 1.64 V/nm (e) and -1.64 V/nm (f) on the electron-doping side. Electron-doped superconductivity can be only observed at negative *D*. The main results closely resemble those observed at $D = \pm 1.55$ V/nm, as illustrated in Fig. 3.



Extended Data Fig. 9. Determination of the in-plane critical magnetic field at the zerotemperature limit $B_{c||}^{0}$. a-c, R_{xx} as a function of T and B_{\parallel} at $n = -0.53 \times 10^{12}$ cm⁻² (a), $n = -0.55 \times 10^{12}$ cm⁻² (**b**), and $n = -0.59 \times 10^{12}$ cm⁻² (**c**) for D = 0.96 V/nm. **d-f**, R_{xx} as a function of T and B_{\parallel} at n = 0.9× 10^{12} cm⁻² (d), $n = 0.89 \times 10^{12}$ cm⁻² (e) and $n = 0.87 \times 10^{12}$ cm⁻² (f) for D = -1.64 V/nm. The opaque circles in each panel depict the critical in-plane magnetic field $B_{c||}$ as a function of T, where the $B_{c||}$ is defined as the field where R_{xx} is 50% of the normal state resistance. The data points in each panel are fitted well by the phenomenological relation $T/T_c^0 = 1 - (B_{c||}/B_{c||}^0)^2$. The green markers indicate the Paulilimit field B_P . Blue lines are plotted based on the formula $T/T_c^0 = 1 - (B_{c\parallel}^2/B_P B_{SOC})$ for an Ising superconductor, where B_{SOC} is obtained from our measurement shown in Extended Data Fig. 1. It can be seen that, even for the hole-doped superconductivity, the measured B_{\parallel} is still smaller than the values expected for an Ising superconductor. Such discrepancy may depend on multiple details, including the Fermi surface shape, the Rashba SOC, the spin Zeeman effect, and the orbital effect of B_{\parallel} . As a general trend, the Ising SOC enhances PVR, while additional Rashba SOC and orbital effect from B_{\parallel} suppresses PVR. Therefore, the value of PVR becomes a quantitative problem given these competing effects. On the other hand, quantitative estimation of quantities such as Rashba SOC, and orbital g-factor of the inplane magnetic field is a nontrivial task, since they all have a small energy scale and are all subjected to renormalization by the electron Coulomb interaction. This makes it challenging to theoretically estimate the value of PVR. Nevertheless, the hole-doped superconductivity clearly violates the Pauli paramagnetic limit, consistent with previous studies^{20,21}. However, the limited resilience to B_{\parallel} observed in electron-doped superconductivity is more puzzling, as a comparable Ising SOC effect is evident in the CB at negative D fields based on the FFT analysis of quantum oscillations.



Extended Data Fig. 10. More data about the in-plane magnetic field dependence of superconducting states. a-d, R_{xx} as a function of *n* and B_{\parallel} for hole-doped superconducting domes at D = 1.19 V/nm (a), D = 1.35 V/nm (b), and for electron-doped superconducting domes at D = -1.47 V/nm (c) and D = -1.55 V/nm (d), measured at T = 20 mK. The superconducting dome width in *n* at D = 1.19 V/nm is almost unchanged under $B_{\parallel} = 1$ T. At D = 1.35 V/nm, the hole-doped superconductivity around -1×10^{12} cm⁻² could still survive under $B_{\parallel} = 1$ T. The highest in-plane magnetic field applied is limited to 1 T due to the magnet limitation of the refrigerator used for the measurement. The Pauli violation ratio $B_{C\parallel}^0/B_p$ at the optimal doping should be significantly larger than 1.4 in **a**, and ~ 2.1 in **b**. On the contrary, the electron-doped superconductivity in **c** and **d** is readily suppressed under a small applied B_{\parallel} (about 0.2 – 0.3 T). The $B_{C\parallel}^0/B_p$ at the optimal doping for **c** and **d** is about 0.31 and 0.25, respectively, significantly below the Pauli paramagnetic limit.



Extended Data Fig. 11. Device image and the measurement configuration. a, Optical image of the BBG/WSe₂ heterostructure device. The device is shaped into a hall bar geometry and the hall bar channel is fabricated in a bubble-free region. The scale bar is 5 μ m. **b**, The schematic of the hall bar device in **a**, along with the illustration of the transport measurement configuration.



Extended Data Fig. 12. The perpendicular magnetic field B_{\perp} dependence of the hole- and electrondoped superconducting states. a-d, R_{xx} as a function of n and B_{\perp} measured at T = 20 mK with D = 1.0V/nm (a), 1.27 V/nm (b) for hole-doped superconducting domes, and D = -1.47 V/nm (c), and -1.55 V/nm (d) for electron-doped superconducting domes, respectively. The critical perpendicular magnetic fields $B_{c\perp}$ for the hole- and electron-doped superconductivity are comparable, which range from about 5 mT to 15 mT.